# Abstracts

## Silicon Permeable Base Transistors for Low-Phase-Noise Oscillator Applications Up to 20 GHz

*D.D. Rathman and W.K. Niblack. "Silicon Permeable Base Transistors for Low-Phase-Noise Oscillator Applications Up to 20 GHz." 1988 MTT-S International Microwave Symposium Digest 88.1 (1988 Vol. I [MWSYM]): 537-540.*

Silicon permeable base transistors have been fabricated that exhibit a small-signal short-circuit current gain frequency exceeding 20 GHz and a maximum frequency of oscillation near 30 GHz. This transistor has been used to realize voltage-controlled oscillators at C, X, and Ku band that have provided low phase noise.

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